Wai Yuen Fu

List of Publications by Year
in descending order

46	985	430442 18	433756 31
papers	citations	h-index	g-index

47	47	47	1238
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Tunable optoelectronic and ferroelectric properties in Sc-based III-nitrides. Journal of Applied Physics, 2013, 114, .	1.1	124
2	Monolithically integrated InGaN/GaN light-emitting diodes, photodetectors, and waveguides on Si substrate. Optica, 2018, 5, 564.	4.8	102
3	Elastic constants and critical thicknesses of ScGaN and ScAlN. Journal of Applied Physics, 2013, 114, .	1.1	93
4	Wafer-scale Fabrication of Non-Polar Mesoporous GaN Distributed Bragg Reflectors via Electrochemical Porosification. Scientific Reports, 2017, 7, 45344.	1.6	47
5	Indium clustering in a-plane InGaN quantum wells as evidenced by atom probe tomography. Applied Physics Letters, 2015, 106, .	1.5	46
6	Chip-scale GaN integration. Progress in Quantum Electronics, 2020, 70, 100247.	3.5	42
7	Geometrical Shaping of InGaN Light-Emitting Diodes by Laser Micromachining. IEEE Photonics Technology Letters, 2009, 21, 1078-1080.	1.3	41
8	Monolithic Integration of GaN-on-Sapphire Light-Emitting Diodes, Photodetectors, and Waveguides. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-6.	1.9	39
9	Structure and strain relaxation effects of defects in InxGa1â^'xN epilayers. Journal of Applied Physics, 2014, 116, .	1.1	38
10	Intensity-Stabilized LEDs With Monolithically Integrated Photodetectors. IEEE Transactions on Industrial Electronics, 2019, 66, 7426-7432.	5.2	36
11	Close-packed hemiellipsoid arrays: A photonic band gap structure patterned by nanosphere lithography. Applied Physics Letters, 2009, 95, 133125.	1.5	33
12	Nanocathodoluminescence Reveals Mitigation of the Stark Shift in InGaN Quantum Wells by Si Doping. Nano Letters, 2015, 15, 7639-7643.	4.5	33
13	Polychromatic light-emitting diodes with a fluorescent nanosphere opal coating. Nanotechnology, 2008, 19, 355203.	1.3	32
14	Evaluation of InGaN/GaN light-emitting diodes of circular geometry. Optics Express, 2009, 17, 22311.	1.7	31
15	InGaN RGB Light-Emitting Diodes With Monolithically Integrated Photodetectors for Stabilizing Color Chromaticity. IEEE Transactions on Industrial Electronics, 2020, 67, 5154-5160.	5.2	29
16	The atomic structure of polar and non-polar InGaN quantum wells and the green gap problem. Ultramicroscopy, 2017, 176, 93-98.	0.8	24
17	The microstructure of non-polar a-plane (112Â¯0) InGaN quantum wells. Journal of Applied Physics, 2016, 119, .	1.1	22
18	Growth of non-polar (11-20) InGaN quantum dots by metal organic vapour phase epitaxy using a two temperature method. APL Materials, 2014, 2, .	2.2	18

#	Article	IF	Citations
19	GaN microdisk with direct coupled waveguide for unidirectional whispering-gallery mode emission. Optics Letters, 2020, 45, 791.	1.7	16
20	Dislocation core structures in Si-doped GaN. Applied Physics Letters, 2015, 107, .	1.5	15
21	Room temperature photonic crystal band-edge lasing from nanopillar array on GaN patterned by nanosphere lithography. Journal of Applied Physics, 2010, 107, 063104.	1.1	12
22	Metallic nanoparticle array on GaN by microsphere lithography. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S654-S657.	0.8	11
23	Nano-cathodoluminescence reveals the effect of electron damage on the optical properties of nitride optoelectronics and the damage threshold. Journal of Applied Physics, 2016, 120, 165704.	1.1	10
24	Electrically injected whispering-gallery mode InGaN/GaN microdisks. Applied Physics Letters, 2021, 119, 101106.	1.5	10
25	Local carrier recombination and associated dynamics in m-plane InGaN/GaN quantum wells probed by picosecond cathodoluminescence. Applied Physics Letters, 2016, 109, .	1.5	9
26	Explaining relative spectral red shifts in InGaN/GaN micropillars. Optica, 2018, 5, 765.	4.8	9
27	Effect of Size on the Luminescent Efficiency of Perovskite Nanocrystals. ACS Applied Energy Materials, 2019, 2, 6998-7004.	2.5	7
28	GaN PNP Light-Emitting Bipolar Junction Transistor. Journal Physics D: Applied Physics, 0, , .	1.3	7
29	Whispering-gallery mode InGaN microdisks on GaN substrates. Optics Express, 2021, 29, 21280.	1.7	6
30	Insight into the impact of atomic- and nano-scale indium distributions on the optical properties of InGaN/GaN quantum well structures grown on m-plane freestanding GaN substrates. Journal of Applied Physics, 2019, 125, 225704.	1.1	5
31	Phosphor-free InGaN nanopillar white LEDs by random clustering of mono-sized nanospheres. Applied Physics Letters, 2021, 118, .	1.5	5
32	Monolithic InGaN Multicolor Lightâ€Emitting Devices. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	1.2	5
33	Dislocation Climb inc-Plane AlN Films. Applied Physics Express, 2011, 4, 065503.	1.1	4
34	Growth of non-polar InGaN quantum dots with an underlying AlN/GaN distributed Bragg reflector by metal-organic vapour phase epitaxy. Superlattices and Microstructures, 2015, 88, 480-488.	1.4	4
35	Packaging of InGaN stripe-shaped light-emitting diodes. Applied Optics, 2018, 57, 2452.	0.9	4
36	Strain-Induced Spectral Red-Shifting from Nanoscale Frustum Arrays Fabricated over InGaN/GaN Quantum Wells for Light-Emitting Applications. ACS Applied Nano Materials, 2021, 4, 666-672.	2.4	4

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37	Structural Characterisation of Improved GaN Epilayers Grown on a Ge(111) Substrate. Applied Physics Express, 2011, 4, 091001.	1.1	3
38	Difference in linear polarization of biaxially strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">I</mml:mi><mml:msub><mml:mi mathvariant="normal">n</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mi mathvariant="normal">G</mml:mi><mml:msub><mml:mi mathvariant="normal">a</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></r	1.1	3
39	Development of chipscale InGaN RGB displays using strain-relaxed nanosphere-defined nanopillars. Nanotechnology, 2022, 33, 285202.	1.3	2
40	Comparison of lasing characteristics of GaN microdisks with different structures. Journal Physics D: Applied Physics, 2022, 55, 355107.	1.3	2
41	A novel GaN photonic crystal structure comprising nanopillars with inclined sidewalls. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S639-S642.	0.8	1
42	Nanosphere Lithography for Nitride Semiconductors. , 2010, , .		1
43	Room temperature lasing of micropillar with circular grating by liquid immersion laser micromachining. , 2015, , .		0
44	Designing microstructures for bandgap manipulation of InGaN Quantum Wells by k.p simulation coupled with molecular dynamics. , 2018, , .		0
45	InGaN quantum nanodisks in nanopillars fabricated by dry etching of InGaN/GaN MQWs. , 2018, , .		0
46	GaN monolithic integration for lighting and display. , 2019, , .		0